

ABSTRACT OF THE DISCLOSURE

A wet etching method of removing silicon from a substrate includes depositing a layer comprising silicon in elemental form over a substrate. The layer is exposed to an aqueous liquid etching solution comprising a hydroxide and a fluoride, and having a pH of at least 10, under conditions and for a period of time effective to etch the elemental silicon from the substrate. Wet etching can be employed in methods of forming trench isolation, and in other methods. Other aspects and implementations are contemplated.